



IUMRS-ICEM 2018

AUGUST 19(SUN.) - 24(FRI.), 2018 / DAEJEON, KOREA

Session Title	Thin-Film Transistors	Session Code	Fr-H1
Date and Time	2018-08-24 / 8:30 - 10:30		
Place	Room H		
Session Chair	TBA		

Fr-H1-1

8:30 - 9:00

[Invited]Improvement in Performance of Metal Oxide Thin-Film Transistors by Modifying a Channel Composition and Structure

Jae Kyeong Jeong
Hanyang Univ., Korea

Fr-H1-2

9:00 - 9:15

Characterization of the Self-Heating Effect in IGZO Thin Film Transistors using Pulse Measurements

Manh-Cuong Nguyen¹, Sang-woo Kim¹, Jaekyeong Jeong², Rino Choi¹, Nuri On², Hyungmin Ji¹, Hoang-Thuy-An Nguyen¹, Sujin Choi¹, Jonggyu Cheon¹, Kyoung-Mun Yu¹, Seong-Yeong Cho¹, and Jin-Hyun Kim¹
¹Inha Univ., Korea, ²Hanyang Univ., Korea

Fr-H1-3

9:15 - 9:30

A New Solution-Processable BODIPY-Acetylene Semiconductor for N-Channel Organic Field-Effect Transistors

Dongil Ho and Choongik Kim
Sogang Univ., Korea

Fr-H1-4

9:30 - 9:45

Influence of High Doping Concentration on Contact Resistivity Measurement with Transmission Line Model and Circular Transmission Line Model

Hyunsu Shin, Seran Park, Eunjung Ko, and Dae-Hong Ko
Yonsei Univ, Korea

Fr-H1-5

9:45 - 10:00

Effect of Oxygen Content on the Stability of Nitrogen-Doped P-Type ZnO Films Fabricated by Reactive Magnetron Sputtering

Faizan Husian, Jian-yuan Chen, and Jyh-Shiarn Cherng
Ming Chi Univ. of Tech., Taiwan